

國立中正大學

112 學年度碩士班招生考試

試題

[第 1 節]

科目名稱	電磁學
系所組別	電機工程學系-電磁晶片組

—作答注意事項—

※作答前請先核對「試題」、「試卷」與「准考證」之系所組別、科目名稱是否相符。

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6. 試題須隨試卷繳還。

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科目名稱：電磁學

本科目共 2 頁 第 1 頁

系所組別：電機工程學系-電磁晶片組

1. (5%) Find ∇V for the scalar function $V = 2r^2 \cos^2 \phi$.

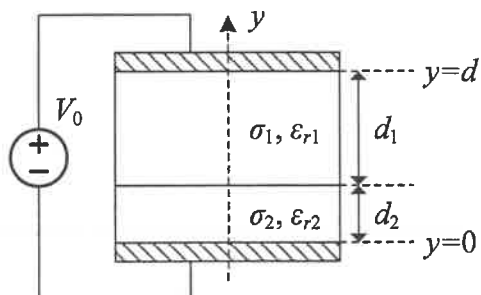


Fig. 1

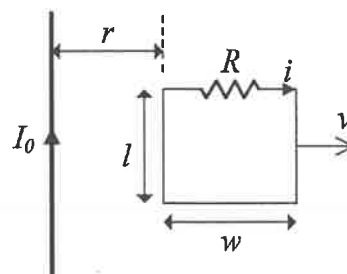


Fig. 2

2. (15%) An dc voltage V_0 is applied across a parallel-plate capacitor of area S as shown in Fig. 1. The space between the metal plates is filled with two different lossy dielectrics of thickness d_1 and d_2 , dielectric constants ϵ_{r1} and ϵ_{r2} , and conductivities σ_1 and σ_2 , respectively. Given $V_0 = 5$ V, $d_1 = 1$ mm, $d_2 = 0.5$ mm, $\sigma_1 = 2$ S/m, $\sigma_2 = 5$ S/m, $\epsilon_{r1} = 4.4$ and $\epsilon_{r2} = 2.2$, respectively, determine
- (3%) The current density J between the plates.
 - (4%) The electric field intensities E in both dielectrics.
 - (4%) The surface charge densities on the metal plates
 - (4%) The surface charge density at the interface.

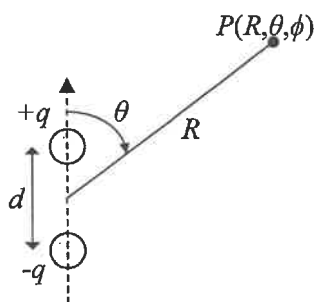


Fig. 3

3. (10%) Given a 4.0 cm radius solid wire centered on the z -axis with a volume current density $J = a_z 8r$ A/cm³ (for r in cm), calculate and plot the magnetic field intensity H versus radial distance from the z -axis over the range $0 \leq r \leq 10$ cm.
4. (10%) A rectangular loop is moving with velocity v radially away from a wire that carries a dc current I_0 as shown in Fig. 2. Determine:
- (5%) The magnetic flux through the loop as a function of time.
 - (5%) An expression for the current induced in the loop as a function of time.
5. (10%) An electric dipole as shown in Fig. 3 consists of positive charge $+q = 10e$ and negative charge $-q = -10e$ with a small separation of 5×10^{-12} m, where $e = 1.6 \times 10^{-19}$ C is the elementary charge. Find:
- (3%) The dipole moment of the electric dipole.

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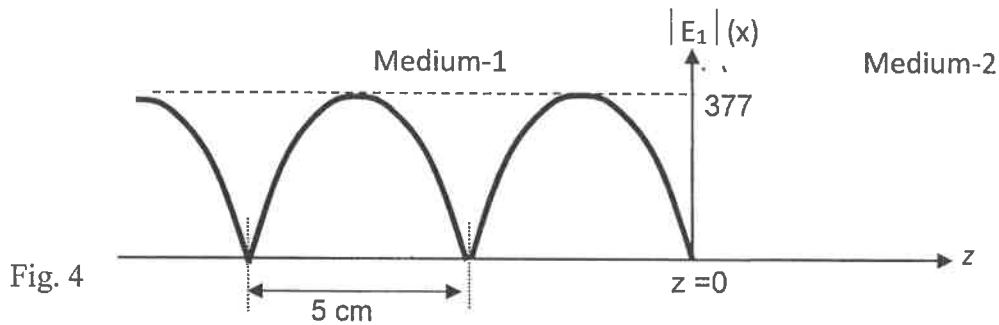
科目名稱：電磁學

本科目共 2 頁 第 2 頁

系所組別：電機工程學系-電磁晶片組

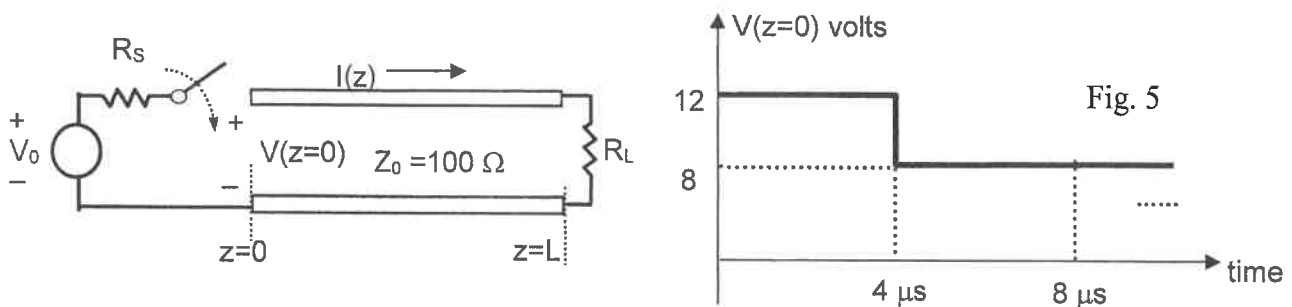
- (b) (3%) The electric potential V at P as $R \gg d$ in terms of spherical coordinates.
 (c) (4%) The electric field intensity E at P as $R \gg d$ in terms of spherical coordinates.

6. (24%) An EM-wave (frequency= 1×10^9 Hz) traveling in a dielectric medium (medium-1) impinges normally upon a perfect conductor (medium-2). Figure below shows the magnitude plot of E-field standing waves generated in medium-1



- (a) (3%) Find the standing wave ratio (SWR)
 (b) (3%) Determine the wavelength λ of this wave.
 (c) (3%) Find the propagation velocity v_p .
 (d) (3%) Determine the propagation constant β of this wave.
 (e) (3%) What is the dielectric constant of medium-1?
 (f) (3%) What is the characteristic impedance of medium-1?
 (g) (6%) Find the mathematical expressions for the incident E-field and H-field.

7. (26%) A 100-Ohm dielectric-filled ($\epsilon_r=2$) transmission line is excited by connecting it to the voltage source at $t = 0$ shown as below. The voltage $V(z=0, t)$ observed at the input of the line is given by :



- (a) (3%) What is the length L of this line?
 (b) (3%) What is the value of the load R_L ?
 (c) (3%) What is the value of the load R_S ?
 (d) (3%) What is the value of generator voltage V_0 ?
 (e) (3%) What is the capacitance C per meter of this transmission line?
 (f) (5%) Plot the bounce (Reflection) diagram (Time vs. z).
 (g) (6%) Plot voltage vs. time observed at $z = 0.4L$.

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試題

[第 1 節]

科目名稱	計算機組織
系所組別	電機工程學系- 計算機工程組 晶片系統組

— 作答注意事項 —

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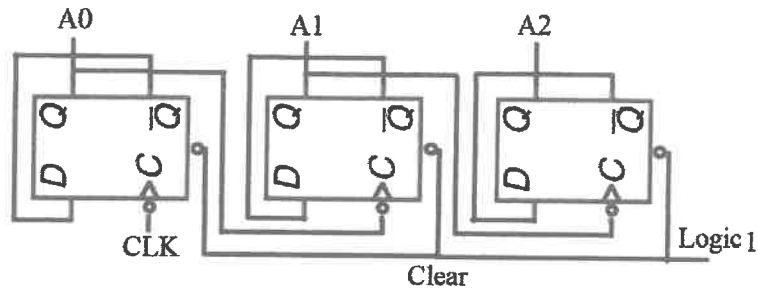
國立中正大學 112 學年度碩士班招生考試試題

科目名稱：計算機組織

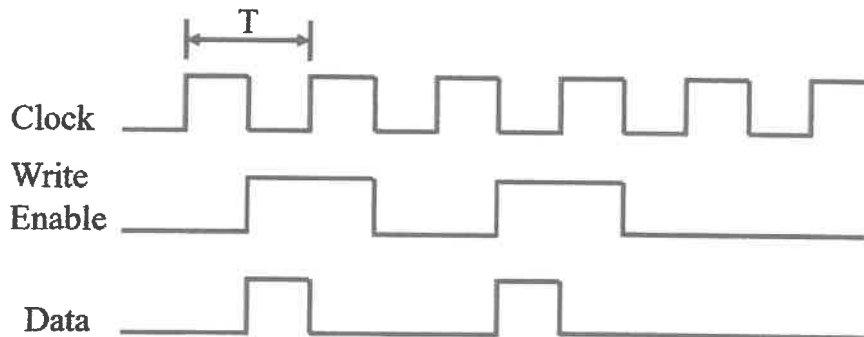
本科目共 2 頁 第 1 頁

系所組別：電機工程學系-計算機工程組、晶片系統組

1. (20%) An engineer designs a watching dog timer for MIPS platform using D type flip-flops as follows. With the initial condition $(Q, \bar{Q}) = (1, 1)$, what are the outputs from A0 to A2 at 5th positive clock edge? Why?



2. (20%) A timing sequence for writing data to the memory is as shown below. Please re-draw a timing sequence with the conditions of (a) memory is triggered by clock's positive edge, (b) write enable is high level triggered, (c) data's hold time is $3/4 T$, (d) data's setup time is $1/2 T$.



3. (20%) Assume two different CPUs designs running with the same instruction set architecture as shown below. The CPU1 is with a clock rate of 2.5 GHz, and the CPU2 is with a clock rate of 3 GHz. Given a program with a dynamic instruction count of $1.0E6$ instructions divided into classes as follows: 10% class A, 20% class B, 50% class C, and 20% class D.

- (a). (10%) Please provide the global CPI for each case?
 (b). (10%) What is the clock cycles required for each CPU design?

	CPI for each instruction class			
	A	B	C	D
CPU1 CPI	1	2	3	3
CPU2 CPI	2	2	2	2

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科目名稱：計算機組織

本科目共 2 頁 第 2 頁

系所組別：電機工程學系-計算機工程組、晶片系統組

4. (20%) Assume the instructions are as follows, and the bne is determined at the output of the register file.
- (a). (10%) Please plot the MIPS five-stage pipeline sequence diagram without forwarding. (10%)
- (b). (10%) Please re-plot the diagram of question (a) with forwarding. (10%)

```
add $10, $21, $9
lw  $9, 20($10)
bne $10, $9, 1000
```

5. (20%) Translate the following loop into C. Assume that the C-level integer i is held in register \$t1, \$s2 holds the C-level integer called *result*, and \$s0 holds the base address of the integer *MemArray*.

```
        addi $t1, $0, 0
LOOP:   lw  $s1, 0($s0)
        add  $s2, $s2, $s1
        addi $s0, $s0, 4
        addi $t1, $t1, 1
        slti $t2, $t1, 100
        bne $t2, $s0, LOOP
```

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試題

[第 1 節]

科目名稱	電路學
系所組別	電機工程學系-電力與電能處理甲組

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國立中正大學 112 學年度碩士班招生考試試題

科目名稱：電路學

本科目共 2 頁 第 1 頁

系所組別：電機工程學系-電力與電能處理甲組

1. For maximum power transfer, what is the value of R_L ? and the max power P_{max} on R_L ? (20%)

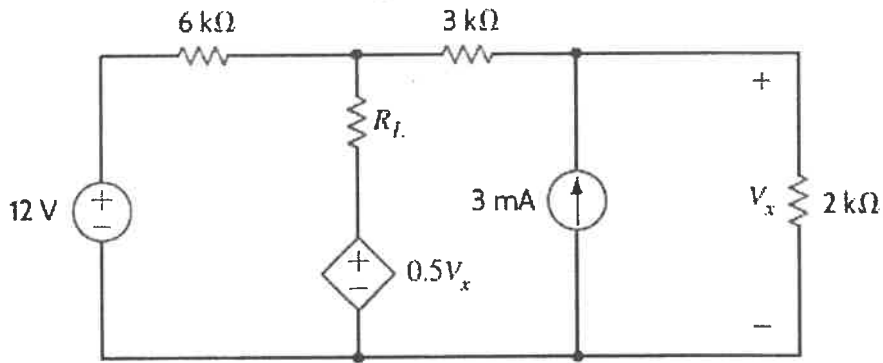


Fig.1

2. In Fig.2, when $t > 0$, Find the transient voltage equation of $v_o(t)$? (20%)

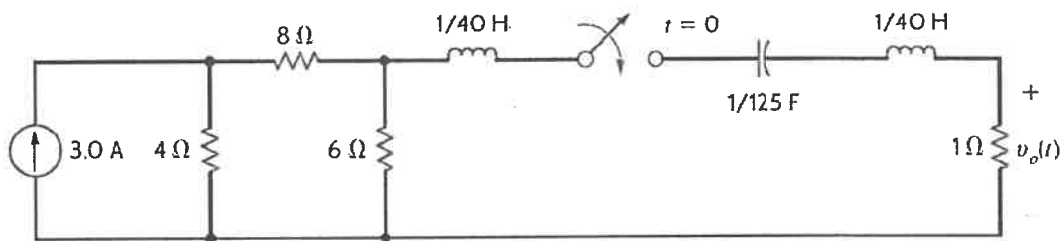


Fig. 2

3. In Fig.3, when $t > 0$, find the transient current equation of $i_L(t)$? (20%)

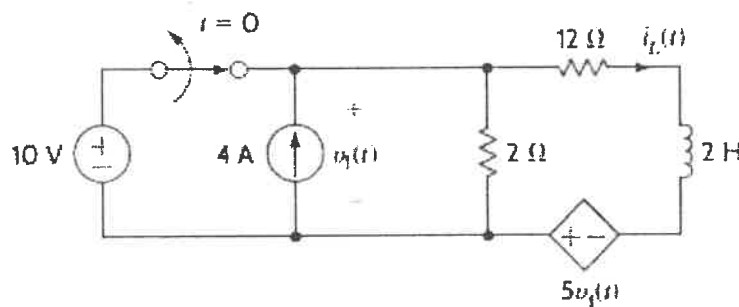


Fig. 3

4. In Fig. 4, determine the value of the inductance L such that the current is in phase with the source voltage $V_s = 13 \cos(600t + 85^\circ)$ V. (20%)

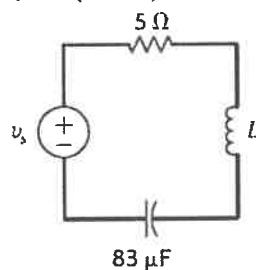


Fig.4

5. In Fig. 5, please find I_o ? (20%)

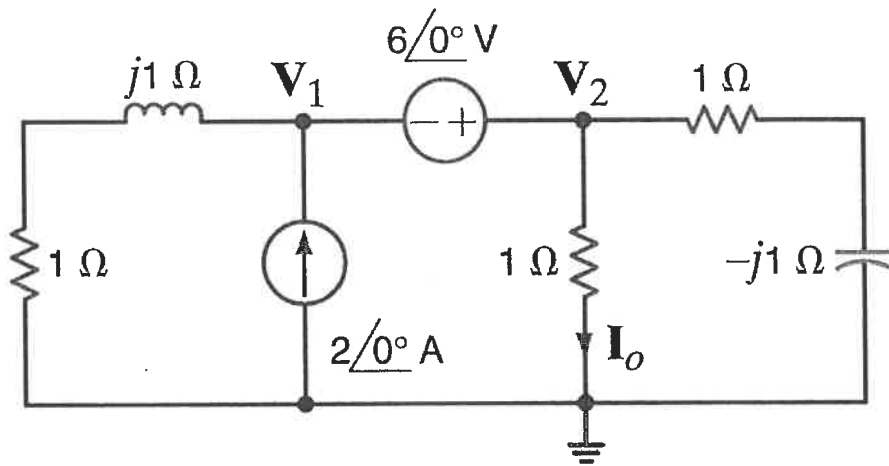


Fig. 5

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試題

[第 1 節]

科目名稱	控制系統
系所組別	電機工程學系-電力與電能處理甲組

—作答注意事項—

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國立中正大學 112 學年度碩士班招生考試試題

科目名稱：控制系統

本科目共 1 頁 第 1 頁

系所組別：電機工程學系-電力與電能處理甲組

1. (20 %) The block diagram of a feedback control system is shown in Fig. 1.

(a) The controller with the transfer function $H(s)$ is for the reduction of the effect of the noise $N(s)$. Find $H(s)$ so that the output $Y(s)$ is totally independent of $N(s)$.

(b) If the maximum overshoot of the unit-step input and the peak time are 10 % and 0.1 sec, respectively. Find the gains F_1 and F_2 when $H(s)$ is as determined in part (a).

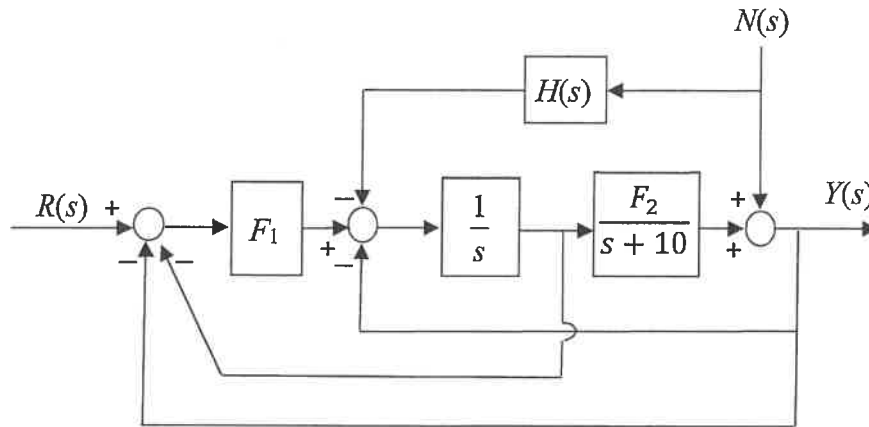


Fig. 1

2. (40 %) The transfer function of a unity feedback control system is

$$G(s) = \frac{F}{s(s+1)(s+5)}$$

(a) Using the Routh-Hurwitz criterion, determine how many roots of the characteristic equation are to the left of the line $s = -1$ in the s -plane for $F = 10$.

(b) Determine if the point $s = -7$ is a point on the loci of roots of the characteristic equation for $F \geq 0$. Use the angle criterion to test this point. If it is a point on a root locus, determine the value of F at this point by using the magnitude criterion.

(c) Using the Nyquist criterion only, find the number of poles of the closed-loop transfer function in the right half-plane, if $F = 5$.

(d) Find the value of F so that the phase margin of the system is 45° .

3. (40%) Given the system $\frac{dx(t)}{dt} = Ax(t) + Bu(t)$, $y(t) = Cx(t)$

where $A = \begin{bmatrix} -1 & 5 \\ -6 & 0 \end{bmatrix}$, $B = \begin{bmatrix} 0 \\ 1 \end{bmatrix}$, $C = [1 \ 0]$.

(a) Determine the controllability and observability of the system.

(b) Let $u(t) = r(t) - Fx(t)$, where $F = [F_1 \ F_2]$ and $r(t)$ is the reference input. Determine if and how controllability and observability of the closed-loop system are affected by the elements of F .

(c) Find the value of F_1 and F_2 such that $\xi = 0.707$ and $\omega_n = 10$ rad/sec.

(d) Find the locus in the F_1 -versus- F_2 plane ($F_1 =$ vertical axis) on which the steady-state error due to a unit-step input is zero.

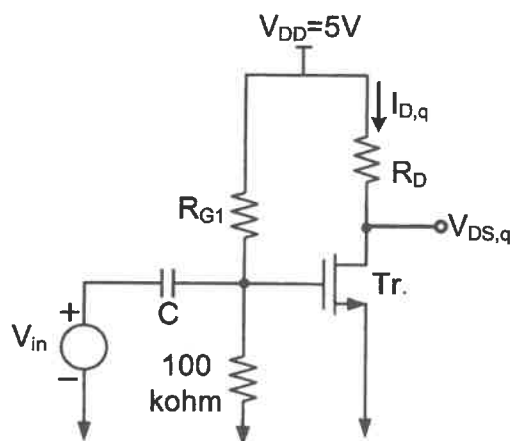
國立中正大學 112 學年度碩士班招生考試試題

科目名稱：電子學

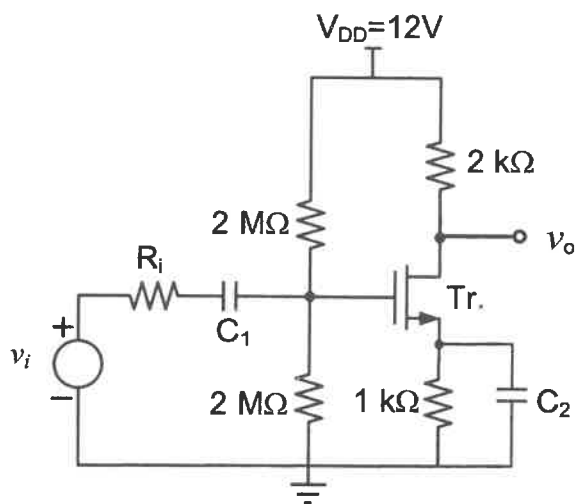
本科目共 4 頁 第 1 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、晶片系統組

1. (10%) In the following circuit, the transistor Tr. operates with $V_T=0.5\text{ V}$, $\mu_n C_{OX} W/2L=0.2\text{ mA/V}^2$, and no channel length modulation effect should be considered. Please properly choose (a) (5%) R_D and (b) (5%) R_{G1} to let the mid-band voltage gain become -4 as $V_{DS,q}$ being 2 V



2. (15%) For a common-source MOSFET amplifier, the transistor Tr. has $V_T = 1\text{ V}$, $\mu_n C_{OX} W/L = 0.2\text{ mA/V}^2$, $C_{gs} = 3\text{ pF}$, $C_{gd} = 2.5\text{ pF}$ and $V_A = 20\text{ V}$, and no channel length modulation effect should be considered. Both of coupling capacitors (C_1 and C_2) are large enough to be short circuits at high frequency
- (a) (5%) What is the 3dB bandwidth if $R_i = 0$
 - (b) (5%) Find the 3dB bandwidth if $R_i = 10\text{ k}\Omega$.
 - (c) (5%) What kind of roles are played by C_1 and C_2 ?



3. (25%) A MOS differential amplifier with $\pm 1\text{-V}$ supplies and 1 mW maximum quiescent power dissipation to provide the differential voltage gain A_d of which being 10 V/V .
- (a) (5%) What is the required V_{ov} to support the input differential signal v_{id} ($=v_{GS1} - v_{GS2}$) being 0.25 V .
 - (b) (5%) What's the transconductance of Q_1 and Q_2 ?
 - (c) (5%) Please explain the role of R_D and the limitation to choose its value?
 - (d) (5%) Assume $k'_n = 500\text{ }\mu\text{A/V}^2$, to specify the required aspect ratio (W/L) as neglecting the Early effect.

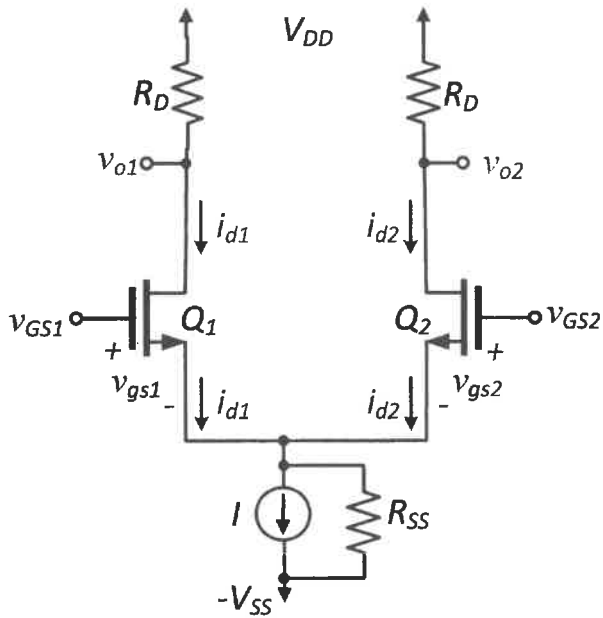
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科目名稱：電子學

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系所組別：電機工程學系-電磁晶片組、計算機工程組、晶片系統組

(e) (5%) Please summarize the effects of R_{SS} happened to differential voltage gain A_d and common-mode voltage gain A_{CM} .



國立中正大學 112 學年度碩士班招生考試試題

科目名稱：電子學

本科目共 4 頁 第 3 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、晶片系統組

4. Fig. P4 shows two applications of op amp. Assuming the op amps used in Fig. P4 are ideal, please answer the following questions:

(1) Find the I_o and R_o indicated in Fig. P4(a). (5%)

(2) If the op amp used in Fig. P4(b) has offset voltage (V_{OS}) of 4 mV, input bias current (I_B) of 1 μ A, and input offset current (I_{OS}) of 0.1 μ A, find the largest dc offset voltage at the output. (10%)

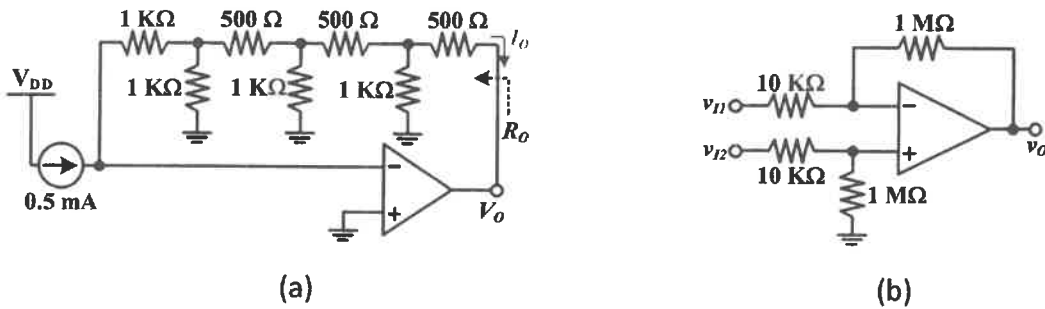


Fig. P4

5. Fig. P5 shows a feedback amplifier, where transistors M_1 , M_2 , and M_3 are biased at saturation region with a bias current of 0.2 mA and an overdrive voltage of 0.4 V. Meanwhile, each current source is implemented using single transistor so that contributes an output resistance. Assume that $|V_A| = 20$ V for all transistors, please find the close-loop gain (v_o/v_i). (20%)

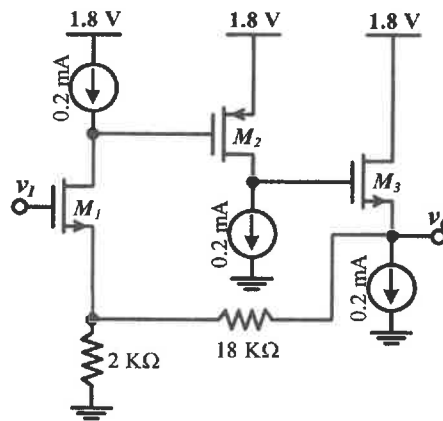


Fig. P5

6. The CMOS logic gate shown in Fig. P6 drives a load capacitance of 10 fF, where the input waveforms are periodic with a cycle time of 1 ns. Please determine the dynamic power dissipation when the logic gate drives the load capacitance with ignoring the short circuit current. (8%)

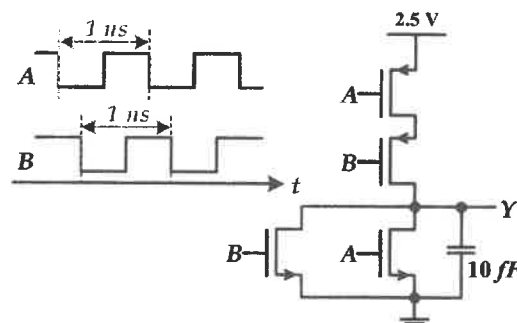


Fig. P6

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科目名稱：電子學

本科目共 4 頁 第 4 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、晶片系統組

7. The CMOS inverter shown in Fig. P7 is fabricated using the following parameters: $V_{TH,n} = |V_{TH,p}| = 0.5 \text{ V}$, $2\mu_p C_{ox} = \mu_n C_{ox} = 100 \mu\text{A}/\text{V}^2$, please find the output voltage of V_Y . (7%)

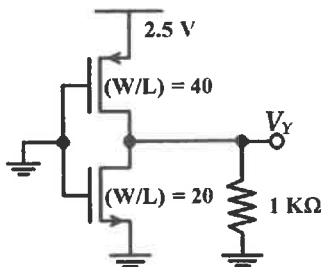


Fig. P7

國立中正大學

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試題

[第 2 節]

科目名稱	線性代數與微分方程
系所組別	電磁晶片組 電機工程學系- 計算機工程組 電力與電能處理甲組

— 作答注意事項 —

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6. 試題須隨試卷繳還。

國立中正大學 112 學年度碩士班招生考試試題

科目名稱：線性代數與微分方程

本科目共 5 頁 第 1 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、電力與電能處理甲組

第一部分：線性代數

Let $\mathbf{A} = [\mathbf{A}^{(1)} \ \mathbf{A}^{(2)} \ \mathbf{A}^{(3)}] = \begin{bmatrix} 1 & 0 & 0 \\ 0 & 2 & 0 \\ 1 & 0 & 2 \end{bmatrix}$, where $\mathbf{A}^{(1)}$, $\mathbf{A}^{(2)}$ and $\mathbf{A}^{(3)}$ are ordered column vectors of \mathbf{A} ,

$\mathbf{B} = [\mathbf{B}^{(1)} \ \mathbf{B}^{(2)} \ \mathbf{B}^{(3)}] = \begin{bmatrix} 2 & 0 & 2 \\ 0 & 1 & 0 \\ 0 & 0 & 1 \end{bmatrix}$, where $\mathbf{B}^{(1)}$, $\mathbf{B}^{(2)}$ and $\mathbf{B}^{(3)}$ are ordered column vectors of \mathbf{B} , and

$\mathbf{I}_3 = [\mathbf{e}_1 \ \mathbf{e}_2 \ \mathbf{e}_3] = \begin{bmatrix} 1 & 0 & 0 \\ 0 & 1 & 0 \\ 0 & 0 & 1 \end{bmatrix}$, where \mathbf{e}_1 , \mathbf{e}_2 and \mathbf{e}_3 are ordered column vectors of \mathbf{I}_3 .

1. Show your answers with details
 - a. (5 pts.) The geometry multiplicities of \mathbf{A} .
 - b. (5 pts.) The product of all eigenvalues in \mathbf{B} .
 - c. (15 pts.) The solution of $\mathbf{A}[x_1 \ x_2 \ x_3]^T = [1 \ 2 \ 3]^T$ with Cramer's rule.

2. In \mathbf{R}^3 , find the results with details.
 - a. (5 pts.) The coordinate vector with the basis $\underline{\mathbf{A}} = \{\mathbf{A}^{(1)}, \mathbf{A}^{(2)}, \mathbf{A}^{(3)}\}$ corresponding to $(1 \ 2 \ 3)_{\underline{\mathbf{e}}}$ with the standard basis $\underline{\mathbf{e}} = \{\mathbf{e}_1, \mathbf{e}_2, \mathbf{e}_3\}$.
 - b. (10 pts.) The coordinate vector with the basis $\underline{\mathbf{A}} = \{\mathbf{A}^{(1)}, \mathbf{A}^{(2)}, \mathbf{A}^{(3)}\}$ corresponding to $(1 \ 2 \ 3)_{\underline{\mathbf{B}}}$ with the basis $\underline{\mathbf{B}} = \{\mathbf{B}^{(1)}, \mathbf{B}^{(2)}, \mathbf{B}^{(3)}\}$.
 - c. (10 pts.) The transition matrix from the standard basis $\underline{\mathbf{B}} = \{\mathbf{B}^{(1)}, \mathbf{B}^{(2)}, \mathbf{B}^{(3)}\}$ to $\underline{\mathbf{A}} = \{\mathbf{A}^{(1)}, \mathbf{A}^{(2)}, \mathbf{A}^{(3)}\}$.

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科目名稱：線性代數與微分方程

本科目共 5 頁 第 2 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、電力與電能處理甲組

第二部分：微分方程

(單一選擇題，每題 5 分，答錯一題，倒扣 2 分，共十題合計 50 分)

1. The differential equation $y' - \frac{y}{x} = y^2$ can be solved using the substitution

Select the correct answer.

- a. $u = y$
- b. $u = y^2$
- c. $u = y^3$
- d. $u = y^{-1}$
- e. $u = y^{-2}$

2. Solve the problem $y' = (x+1)y$, $y(0) = 1$ numerically for $y(0.2)$ using step size of $h=0.1$.

Select the correct answer.

- a. 1.1
- b. 1.11
- c. 1.2
- d. 1.21
- e. 1.221

3. The solution of the differential equation $x^2y'' - 5xy' + 5y = 0$ is

Select the correct answer.

- a. $y = c_1x + c_2x^2$
- b. $y = c_1x\cos(\ln x) + c_2x^2\sin(\ln x)$
- c. $y = c_1x\cos(2\ln x) + c_2x^2\sin(2\ln x)$
- d. $y = c_1x^{\frac{(5+\sqrt{5})}{2}} + c_2x^{\frac{(5-\sqrt{5})}{2}}$
- e. $y = c_1e^{2x} + c_2xe^{2x}\sin x$

4. Write the differential equation for RLC series electrical circuit if $L=0.25$ H, $R=10 \Omega$, and $C=0.001$ F, and $E(t)=0$.

Select the correct answer.

- a. $\frac{1}{4} \frac{d^2q}{dt^2} + 10 \frac{dq}{dt} + 1000q = 0$
- b. $\frac{1}{4} \frac{d^2q}{dt^2} + 10 \frac{dq}{dt} + \frac{1}{1000}q = 0$

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科目名稱：線性代數與微分方程

本科目共 5 頁 第 3 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、電力與電能處理甲組

c.
$$\frac{1}{4} \frac{d^2 q}{dt^2} + 10 \frac{dq}{dt} + 1000q = 100$$

d.
$$\frac{d^2 q}{dt^2} + 10 \frac{dq}{dt} + 1000q = \frac{1}{4}$$

e.
$$\frac{1}{4} \frac{d^2 q}{dt^2} + \frac{dq}{dt} + 1000q = 10$$

5. In the previous problem, find the charge $q(t)$ on the capacitor in an RLC series circuit if $q(0)=5$ C, and $i(0)=0$ A .

Select the correct answer.

a.
$$q(t) = \frac{5\sqrt{10}}{3} e^{-20t} \sin(60t + 1.249)$$

b.
$$q(t) = \frac{5\sqrt{10}}{3} e^{-10t} \sin(60t + 1.249)$$

c.
$$q(t) = \frac{\sqrt{10}}{3} e^t \sin(60t + 1.249)$$

d.
$$q(t) = \frac{5\sqrt{10}}{3} e^{20t} \sin(60t + 1.249)$$

e.
$$q(t) = \frac{5\sqrt{10}}{3} e^{-20t}$$

6. The particular solution of $X' = \begin{bmatrix} 2 & 3 \\ 2 & 1 \end{bmatrix} X + \begin{bmatrix} t \\ 1 \end{bmatrix}$ is

Select the correct answer.

a.
$$\begin{bmatrix} \frac{t}{4} + \frac{19}{16} \\ \frac{t}{2} + \frac{7}{8} \end{bmatrix}$$

b.
$$\begin{bmatrix} \frac{t}{4} - \frac{19}{16} \\ \frac{t}{2} + \frac{7}{8} \end{bmatrix}$$

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科目名稱：線性代數與微分方程

本科目共 5 頁 第 4 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、電力與電能處理甲組

c.
$$\begin{bmatrix} \frac{t}{4} + \frac{1}{8} \\ t - \frac{7}{8} \end{bmatrix}$$

d.
$$\begin{bmatrix} \frac{t}{4} - \frac{1}{8} \\ t - \frac{7}{8} \end{bmatrix}$$

e. None of the above

7. The Fourier series of the function $f(x) = x^2$ on $[-1, 1]$ is

Select the correct answer.

a.
$$\sum_{n=1}^{\infty} \frac{4(-1)^n \sin(n\pi x)}{n^2 \pi^2} + \sum_{n=1}^{\infty} \frac{4(-1)^n \cos(n\pi x)}{n^2 \pi^2}$$

b.
$$\sum_{n=1}^{\infty} \frac{4(-1)^n \sin(n\pi x)}{n^2 \pi^2}$$

c.
$$\sum_{n=1}^{\infty} \frac{4(-1)^n \cos(n\pi x)}{n^2 \pi^2}$$

d.
$$\frac{1}{3} + \sum_{n=1}^{\infty} \frac{4(-1)^n \sin(n\pi x)}{n^2 \pi^2}$$

e.
$$\frac{1}{3} + \sum_{n=1}^{\infty} \frac{4(-1)^n \cos(n\pi x)}{n^2 \pi^2}$$

8. The general solution of $y'' + n^2 \pi^2 y = 0$, $y(0) = 0$, $y(1) = 1$, $n = 1, 2, 3, \dots$, is

Select the correct answer.

a. $y = 0$

b. $y = c \cdot \sin(n\pi x)$

c. $y = c \cdot \cos(n\pi x)$

d. $y = c(e^{n\pi x} - e^{-n\pi x})$

e. $y = c(e^{n\pi x} + e^{-n\pi x})$

9. When the Laplace transform is applied to the problem

$y'' + 2y' + y = e^{3t}$, $y(0) = 1$, $y'(0) = 2$, the resulting transformed equation is

Select the correct answer

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科目名稱：線性代數與微分方程

本科目共 5 頁 第 5 頁

系所組別：電機工程學系-電磁晶片組、計算機工程組、電力與電能處理甲組

a. $(s^2 + 2s + 1)Y = -s - 4 + \frac{1}{s - 3}$

b. $(s^2 + 2s + 1)Y = s - 4 + \frac{1}{s - 3}$

c. $(s^2 + 2s + 1)Y = s + 4 + \frac{1}{s + 3}$

d. $(s^2 + 2s + 1)Y = -s - 4 + \frac{1}{s + 3}$

e. $(s^2 + 2s + 1)Y = s + 4 + \frac{1}{s - 3}$

10. The solution of the initial value problem in the previous problem is

Select the correct answer

a. $y = \frac{15e^t + 44te^t + e^{3t}}{16}$

b. $y = \frac{15e^t - 44te^t + e^{3t}}{16}$

c. $y = \frac{15e^{-t} + 44te^{-t} + e^{3t}}{16}$

d. $y = \frac{15e^{-t} - 44te^{-t} + e^{3t}}{8}$

e. $y = \frac{15e^{-t} + 44te^{-t} + e^{3t}}{8}$

國立中正大學

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試題

[第 2 節]

科目名稱	資料結構
系所組別	電機工程學系-計算機工程組

—作答注意事項—

※作答前請先核對「試題」、「試卷」與「准考證」之系所組別、科目名稱是否相符。

1. 預備鈴響時即可入場，但至考試開始鈴響前，不得翻閱試題，並不得書寫、畫記、作答。
2. 考試開始鈴響時，即可開始作答；考試結束鈴響畢，應即停止作答。
3. 入場後於考試開始 40 分鐘內不得離場。
4. 全部答題均須在試卷（答案卷）作答區內完成。
5. 試卷作答限用藍色或黑色筆（含鉛筆）書寫。
6. 試題須隨試卷繳還。

1. Binary Search Tree (BST)

Complete the breadth first traversal on a BST using a queue. Answer the following questions.

- i. (5 points) Draw a diagram to the design of your queue and explain how you can apply the concept of ADT (abstract data type) in your design. Explain your strategy of using a queue to perform the breadth first traversal.
- ii. (5 points) Define the data structures of the queue described above using C or pseudo code.
- iii. (15 points) Define the following operations to the queue:
 - 1) NewQ: to create and initialize a queue to use.
 - 2) EnQ: to perform enqueue
 - 3) DeQ: to perform dequeue
- iv. (10 points) Define a function which performs the breadth first traversal on a BST. Use C or pseudo code to complete your answer. Be sure to define the function header and local variables clearly.

2. Sorting

- i. (15 points) Define the function to perform the **Selection Sort** on an integer array. The sorted array is in ascending order. Use C or pseudo code to complete your answer. Be sure to define the function header and local variables clearly.
- ii. (10 points) Analyze the time complexity of the function above and show the result in the Big-O notation. Be sure to show the steps of analysis with your explanation and the associated detail calculation.

3. Application

Consider a string defined by a linked list of characters illustrate here, in which a string "HELLO" is represented. For the questions below, use C or pseudo code to complete your answers. Be sure to define the function header and local variables clearly.



- i. (5 points) Design the data structure of a node with a field storing a single character and a pointer to the next node.
- ii. (15 points) Write the function to perform string comparison on two such strings.
- iii. (10 points) Write the function to perform string copy to produce a new string based on a given string. Be sure to create a new string and not just having a pointer pointing to the given string.
- iv. (10 points) Write the function to free the memory of all nodes in a given list.